

2PB709ART

45 V, 100 mA PNP general-purpose transistor Rev. 01 — 19 March 2007

Product data sheet

Product profile

1.1 General description

PNP general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: 2PD601ART.

1.2 Features

- General-purpose transistor
- Small SMD plastic package

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
I _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -2 \text{ mA}$	210	-	340	

2. Pinning information

Table 2. **Pinning**

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 —
			sym013



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3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
2PB709ART	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
2PB709ART	C5*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

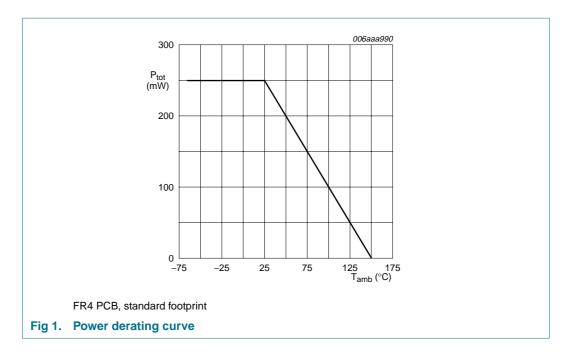
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-45	V
V_{CEO}	collector-emitter voltage	open base	-	-45	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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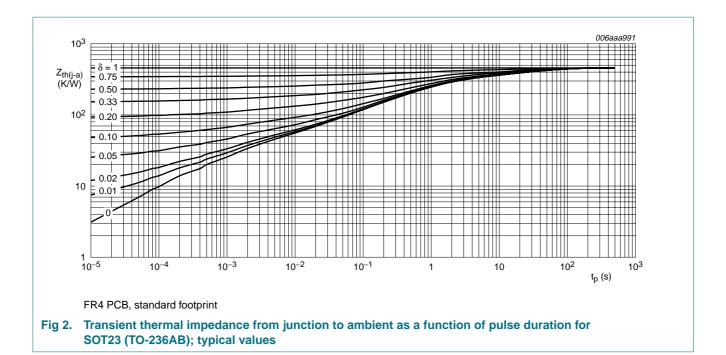
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] _	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	140	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

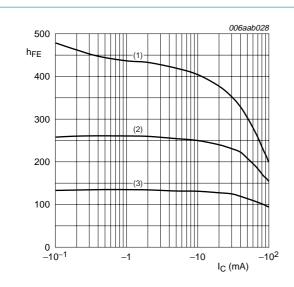
Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -45 \text{ V}; I_E = 0 \text{ A}$	-	-	-10	nA
	current	$V_{CB} = -45 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	- 5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	–10	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -2 \text{ mA}$	210	-	340	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100 \text{ mA};$ $I_B = -10 \text{ mA}$	<u>[1]</u> -	-	-500	mV
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -1 \text{ mA};$ f = 100 MHz	70	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	5	pF

^[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

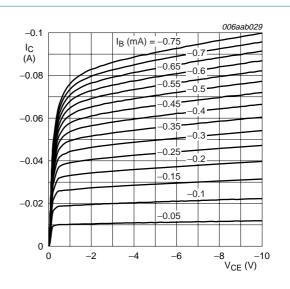
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$$V_{CE} = -10 \text{ V}$$

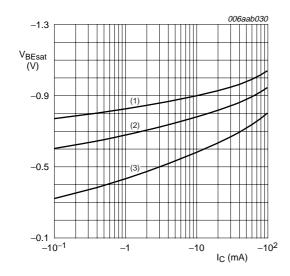
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



T_{amb} = 25 °C

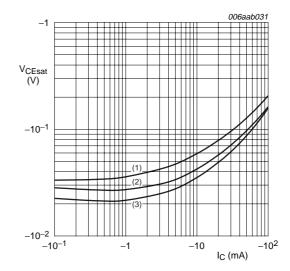
Fig 4. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) T_{amb} = 150 °C

Fig 5. Base-emitter saturation voltage as a function of collector current; typical values



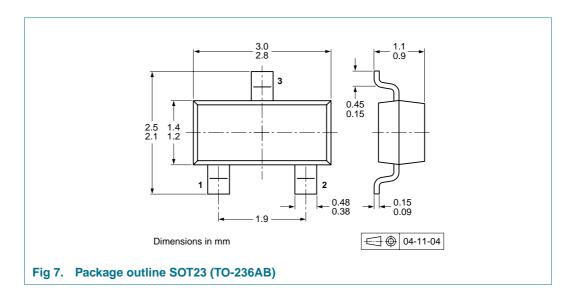
 $I_{\rm C}/I_{\rm B} = 10$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values

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8. Package outline

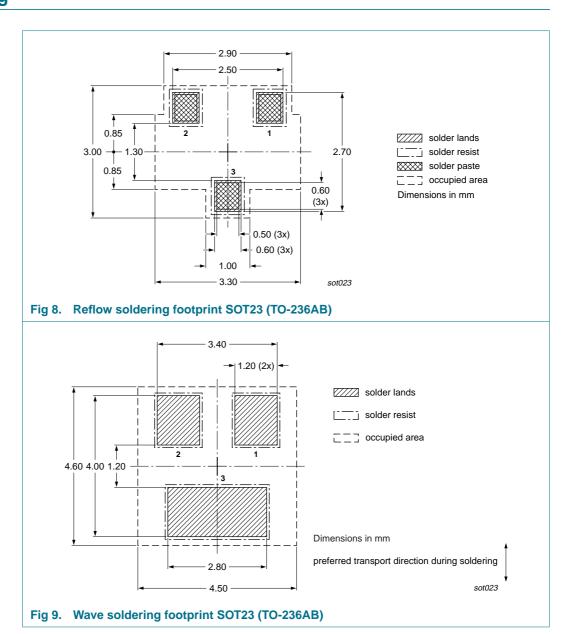


9. Packing information

Please refer to packing information on www.nexperia.com.

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10. Soldering



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11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
2PB709ART	20070319	Product data sheet	-	-

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12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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